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### (54) DEVICE FOR ELECTROSTATIC DISCHARGE PROTECTION USING SILICON CONTROLLED RECTIFIER

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#### ABSTRACT (57)

A device including a first clamp circuit connected between a first node and a second node, wherein the first clamp circuit includes: a symmetric bipolar transistor comprising a control terminal, a first current terminal and a second current terminal, wherein the first current terminal and the second current terminal are symmetrical to each other with respect to the control terminal; a first bipolar transistor electrically connected to the symmetric bipolar transistor and to the first node; and a second bipolar transistor electrically connected to the symmetric bipolar transistor and to the second node.

